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Vishay Siliconix

N-Channel 20 V (D-S) Fast Switching MOSFET

liew Bottom View

PRODUCT SUMMARY	
V _{DS} (V)	20
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.0049
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0061
Q _g typ. (nC)	20
I _D (A)	22
Configuration	Single

FEATURES

 TrenchFET[®] Gen II power MOSFET for ultra low on-resistance

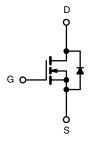


• 100 % R_g tested

Material categorization: for definitions of FREE compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · Synchronous rectification
- Point-of-load converters
- Protection devices
- Hot swap



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH108DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unl	less otherwise	noted)			
PARAMETER	SYMBOL	10 s	STEADY STATE	UNIT		
Drain-source voltage		V_{DS}	20	20		
Gate-source voltage		V_{GS}	± 16	± 16	V	
Continuous drain current (T _J = 150 °C) ^a	T _A = 25 °C	1	22	14		
	T _A = 70 °C	l _D	17.6	11.2		
Pulsed drain current		I _{DM}	60	60	Α	
Continuous source current (diode conduction) ^a		I _S	3.2	1.3		
Single avalanche current	L = 0.1 mH	I _{AS}	22	22		
Single avalanche energy	e avalanche energy		24	24	mJ	
Maximum power dissipation ^a	T _A = 25 °C	Б	3.8	1.5	W	
waximum power dissipation 4	T _A = 70 °C	P_{D}	2.0	0.8	VV	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150		°C	
Soldering recommendations (peak temperature) b, c			260			

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction to ambient 8	t ≤ 10 s	В	24	33	
Maximum junction-to-ambient ^a	Steady state	R_{thJA}	65	81	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	1.9	2.4	

Notes

- a. Surface mounted on 1" x 1" FR4 board
- b. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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PARAMETER	AMETER SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	-	2	V	
Gate body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 16 \text{ V}$	-	-	± 100	nA	
Zava gata valtaga dvain avvvant		V _{DS} = 20 V, V _{GS} = 0 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	5	μA	
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40	=	-	Α	
Drain-source on-state resistance ^a	В	V _{GS} = 10 V, I _D = 22 A	-	0.0041	0.0049	Ω	
	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 19.7 A	-	0.0050	0.0061		
Forward transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 22 A	-	88	-	S	
Diode forward voltage ^a	V _{SD}	I _S = 3.2 A, V _{GS} = 0 V	-	0.75	1.2	V	
Dynamic ^b	<u> </u>						
Total gate charge	Qg		-	20	30	nC	
Gate-source charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 22 \text{ A}$	-	6.3	-		
Gate-drain charge	Q _{gd}		-	4.9	-		
Gate resistance	R_g	f = 1 MHz	0.7	1.4	2.1	Ω	
Turn-on delay time	t _{d(on)}		-	10	15		
Rise time	t _r	V_{DD} = 20 V, R_L = 20 Ω	-	10	15		
Turn-off delay time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω	-	60	130	ns	
Fall time	t _f		-	10	15		
Source-drain reverse recovery time	t _{rr}	1 0 0 0 1:/44 100 0/	-	30	60		
Reverse recovery charge	Q_{rr}	I _F = 3.2 A, di/dt = 100 A/μs		20	36	nC	

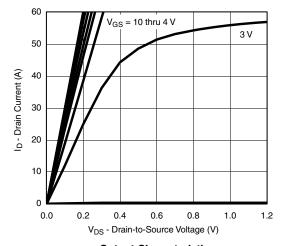
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

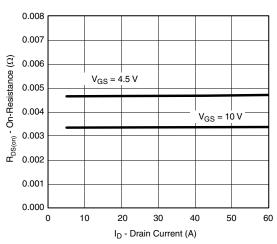
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



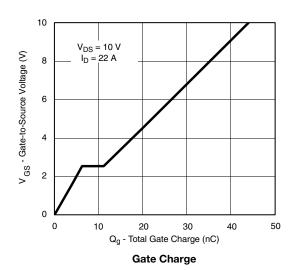
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

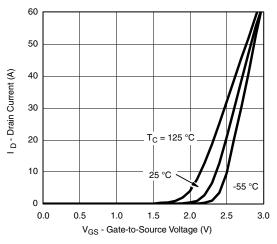


Output Characteristics

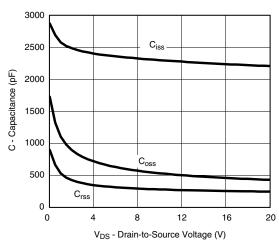


On-Resistance vs. Drain Current

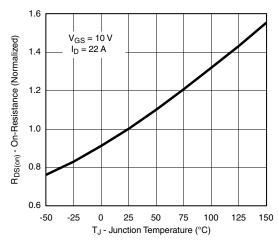




Transfer Characteristics



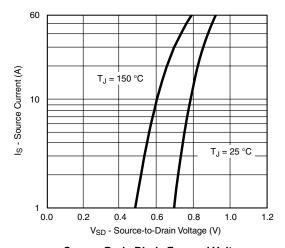
Capacitance



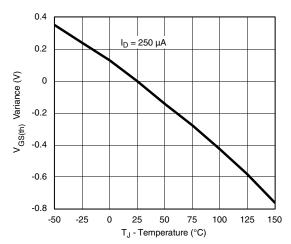
On-Resistance vs. Junction Temperature



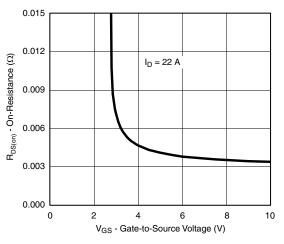
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



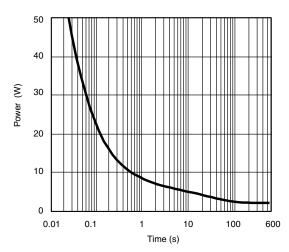
Source-Drain Diode Forward Voltage



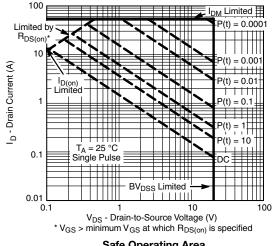
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

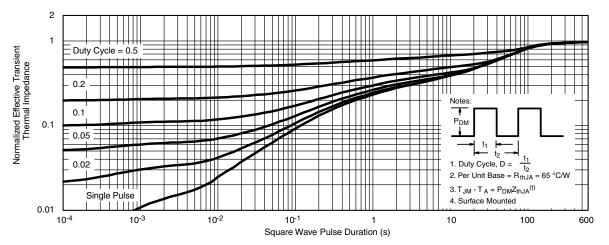


Single Pulse Power, Junction-to-Ambient

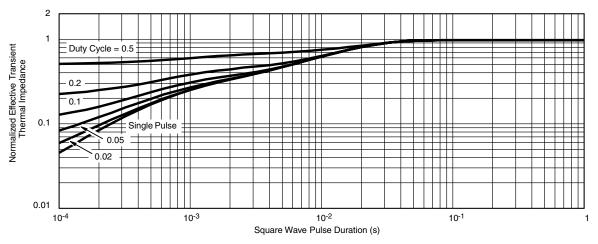




TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

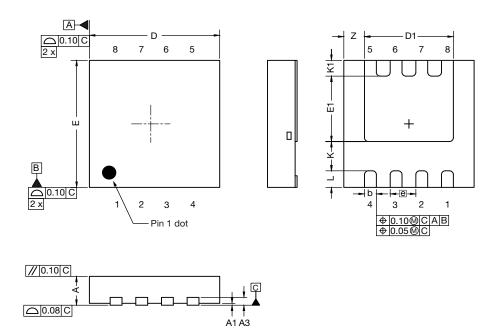


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?79330.

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Case Outline for PowerPAK® 1212-SWLH and PowerPAK® 1212-8SH

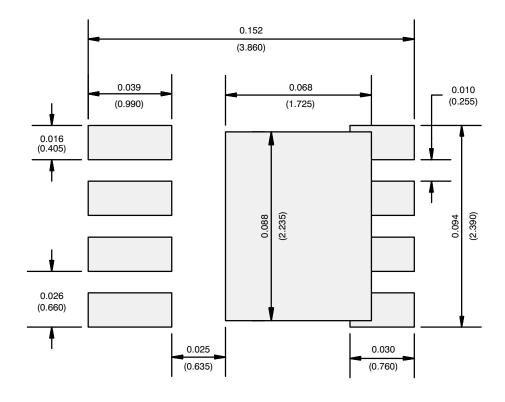


DIM.		MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.82	0.90	0.98	0.032	0.035	0.038	
A1	0.00	-	0.05	0.000	-	0.002	
A3		0.20 ref.			0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.15	2.25	2.35	0.085	0.089	0.093	
Е	3.20	3.30	3.40	0.126	0.130	0.134	
E1	1.60	1.70	1.80	0.063	0.067	0.071	
е		0.65 bsc.			0.026 bsc.		
K		0.76 ref.			0.030 ref.		
K1	0.41 ref.		0.41 ref. 0.016 ref.				
L	0.33	0.43	0.53	0.013	0.017	0.021	
Z	0.525 ref.			0.021 ref.			
	Rev. C, 07-Dec-2020					0.021 ref.	

DWG: 6062



RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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